

the single crystalline film is formed from one of the group of Si, GaN, GaAs, $Ga_{1-x}Al_xAs$, ZnSe, ZnS, CdTe, $ZnS_{1-x}Se_x$, and YBCO.

22. The method of claim 18, wherein:

the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, $SrTiO_3$, and sapphire; and

the single crystalline film is formed from one of the group of Si, GaAs, $Ga_{1-x}Al_xAs$, ZnSe, ZnS, CdTe, $ZnS_{1-x}Se_x$, and YBCO.

23. The method of claim 18 wherein:

the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, and $SrTiO_3$; and

the single crystalline film is formed from one of the group of Si, GaN, GaAs, $Ga_{1-x}Al_xAs$, ZnSe, ZnS, CdTe, $ZnS_{1-x}Se_x$, and YBCO.--